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(54) Title: PLASMA SOURCE HAVING A DIELECTRIC PLASMA CHAMBER WITH IMPROVED PLASMA RESISTANCE

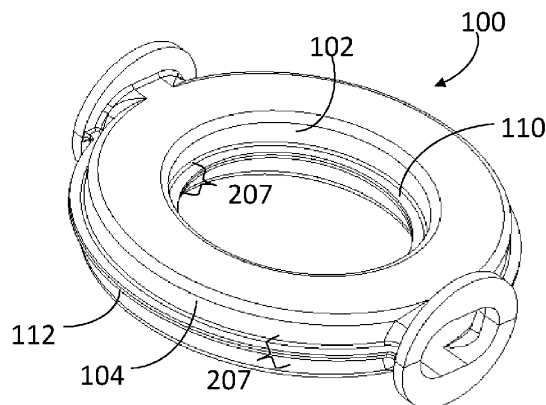


FIG. 1

(57) Abstract: A plasma chamber of a plasma processing system is provided. The plasma chamber defines a plasma channel having a first side and a second side oppositely disposed along a length of the plasma channel. The plasma chamber comprises a first section and a second section constructed from a dielectric material and an interface that bonds together the first and second sections at between a first flange of the first section and a third flange of the second section and between a second flange of the first section and a fourth flange of the second section.

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